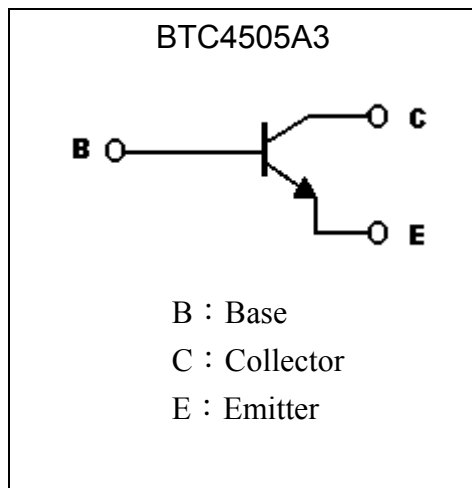
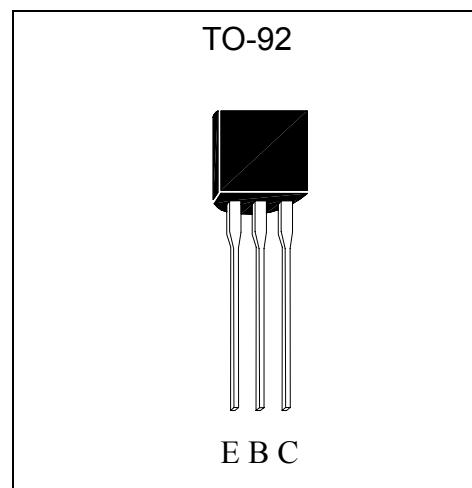


**High Voltage NPN Epitaxial Planar Transistor**

# BTC4505A3

**Features**

- High breakdown voltage. ( $BV_{CEO} = 400V$ )
- Low saturation voltage, typically  $V_{CE(sat)} = 0.1V$  at  $I_C / I_B = 10mA / 1mA$ .
- Complementary to BTA1759A3

**Symbol**

**Outline**

**Absolute Maximum Ratings** ( $T_a = 25^\circ C$ )

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	$V_{CBO}$	400	V
Collector-Emitter Voltage	$V_{CEO}$	400	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	300	mA
Power Dissipation	$P_d$	625	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~+150	$^\circ C$

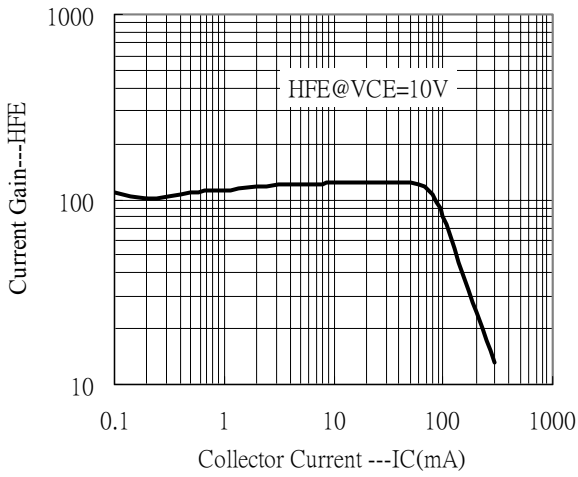
**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	400	-	-	V	I <sub>C</sub> =50μA, I <sub>E</sub> =0
BV <sub>CEO</sub>	400	-	-	V	I <sub>C</sub> =1mA, I <sub>B</sub> =0
BV <sub>EBO</sub>	6	-	-	V	I <sub>E</sub> =50μA, I <sub>C</sub> =0
I <sub>CB0</sub>	-	-	10	μA	V <sub>CB</sub> =400V, I <sub>E</sub> =0
I <sub>CER</sub>	-	-	20	nA	V <sub>CE</sub> =300V, R <sub>EB</sub> =4kΩ
I <sub>EBO</sub>	-	-	10	μA	V <sub>EB</sub> =6V, I <sub>C</sub> =0
*V <sub>CE(sat)</sub>	-	0.1	0.5	V	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA
*V <sub>BE(sat)</sub>	-	-	1.5	V	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA
h <sub>FE</sub>	100	-	270	-	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA
f <sub>T</sub>	-	20	-	MHZ	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA, f=10MHZ
Cob	-	7	-	pF	V <sub>CB</sub> =10V, f=1MHZ

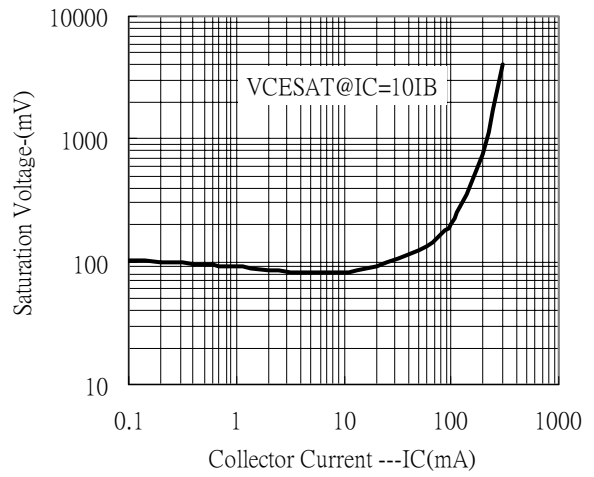
\*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

**Characteristic Curves**

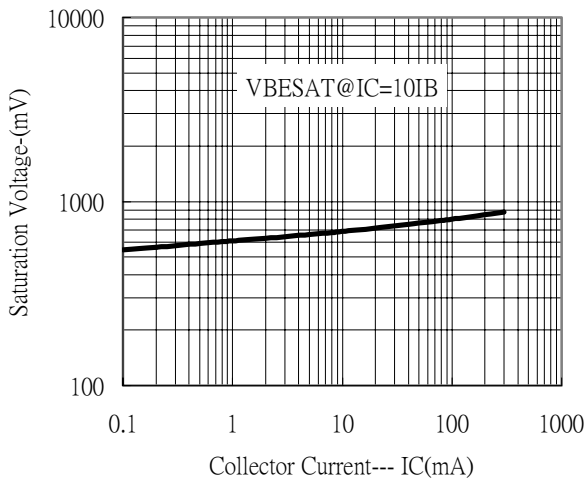
Current Gain vs Collector Current



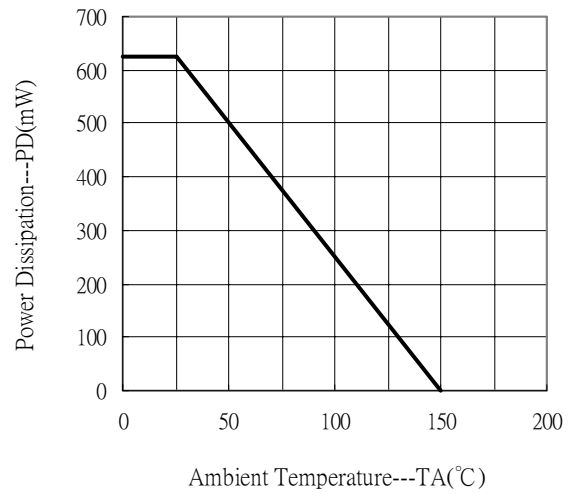
Saturation Voltage vs Collector Current



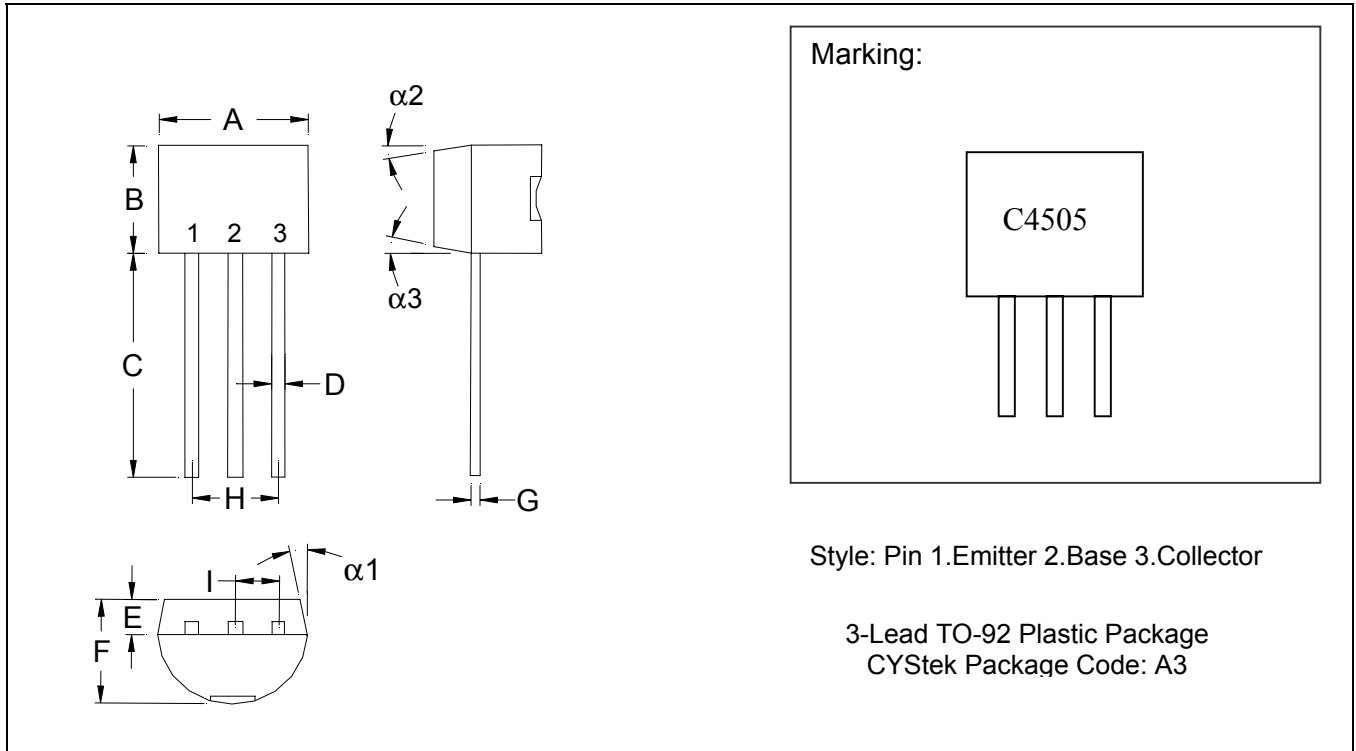
Saturation Voltage vs Collector Current



Power Derating Curve



**TO-92 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°

Notes: 1. Controlling dimension: millimeters.

2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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